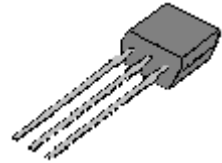


2SC2999

Silicon NPN Transistor

High frequency amplifier applications.

The 2SC2999 is a silicon NPN planar epitaxial transistor in a MINI (TO-92S) type package. This device is suitable for use as Low Noise RF amplifier applications.



ECB

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CBO}	25V
Collector-Emitter Voltage, V_{CEO}	20V
Emitter-Base Voltage, V_{EBO}	3V
Collector Current, I_C	30mA
Total Device Dissipation ($T_A = +25^\circ\text{C}$), P_D	150mW
Operating Junction Temperature, T_J	+125°C
Storage Temperature Range, T_{stg}	-40° to +125°C

Electrical Characteristics:

($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Forward Current Transfer Ratio	h_{FE}	$V_{CE} = 6V, I_C = 1mA$	40	-	200	
Power Gain	PG	$V_{CE} = 6V, I_C = 1mA, f = 100MHz$	-	28	-	dB
Gain-Bandwidth Product	f_T	$I_C = 5mA, V_{CE} = 10V, f = 100MHz$	450	750	-	MHz
Noise Figure	NF	$I_C = 1mA, V_{CB} = 6V, f = 100MHz$	-	2,2	-	dB

